

Product Overview

2SA1943: PNP Epitaxial Silicon Transistor

For complete documentation, see the data sheet.

2SA1943

Features

- High Current Capability: $I_C = -15\text{ A}$
- High Power Dissipation : 150 watts
- High Frequency : 30 MHz
- High Voltage : $V_{CEO} = -250\text{ V}$
- Wide S.O.A for reliable operation
- Excellent Gain Linearity for low THD
- Complement to 2SC5200/FJL4315
- Full thermal and electrical Spice models are available

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CB0} (V)	V_{EB0} (V)	$V_{BE(sat)}$ (V)	$V_{BE(0)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
2SA1943OTU	1.9917	Pb-free Halide free non AEC-Q and PPAP	Active	PNP	General Purpose	3	17	250	250	5	-	1	80	160	30	150	TO-264-3
2SA1943RTU	2.3323	Pb-free Halide free non AEC-Q and PPAP	Active	PNP	General Purpose								55	110	30	150	TO-264-3

For more information please contact your local sales support at www.onsemi.com.

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